

General Description

The ZMD68311M combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. Two N Channel MOSFET inside for dual DIE implication.

Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Dual DIE in one package

Application

- Power Management in Notebook Computer
- BLDC Motor driver

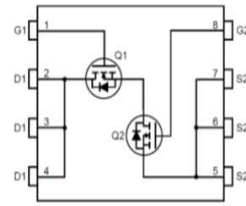
Ordering Information:

Part NO.	ZMD68311M
Marking	68311
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

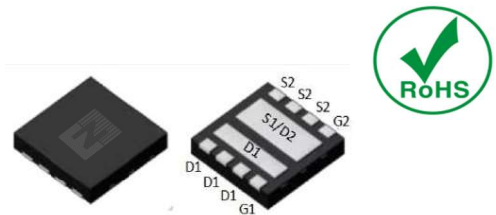
Absolute Maximum Ratings ($T_c = 25^\circ\text{C}$) (Q1)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_D@T_c=25^\circ\text{C}$	12	A
	$I_D@T_c=75^\circ\text{C}$	9.1	A
	$I_D@T_c=100^\circ\text{C}$	7.5	A
Pulsed Drain Current ^①	I_{DM}	36	A
Total Power Dissipation	$P_D@T_c=25^\circ\text{C}$	17	W
Total Power Dissipation	$P_D@T_A=25^\circ\text{C}$	0.9	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 to 150	$^\circ\text{C}$
Single Pulse Avalanche Energy@L=0.1mH	E_{AS}	10	mJ

Product Summary



$V_{DS1} = 30\text{V}$
 $V_{DS2} = 30\text{V}$
 $R_{DS(ON)1} = 10\text{m}\Omega$
 $R_{DS(ON)2} = 8\text{m}\Omega$
 $I_{D1} = 12\text{A}$
 $I_{D2} = 15\text{A}$



DFN3*3

•Thermal resistance(Q1)

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case ^②	R_{thJC}	-	-	7.1	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	140	° C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	° C

•Electronic Characteristics(Q1)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2		2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=12A$		10	13	m Ω
		$V_{GS}=4.5V, I_D=10A$		14	17	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=25V, I_D=10A$		5		S
Source-drain voltage	V_{SD}	$I_S=12A$			1.28	V

•Electronic Characteristics(Q1)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	$V_{DS}=25V$ $f=1MHz$	-	850	-	pF
Output capacitance	C_{oss}		-	190	-	
Reverse transfer capacitance	C_{rss}		-	100	-	

•Gate Charge characteristics($T_a=25^\circ C$)(Q1)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	$V_{DD}=15V$	-	10	-	nC
Gate - Source charge	Q_{gs}	$I_D=12A$	-	3.5	-	
Gate - Drain charge	Q_{gd}	$V_{GS}=10V$	-	5	-	

•Absolute Maximum Ratings (T_C=25°C) (Q2)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current	I _D @T _C =25°C	15	A
	I _D @T _C =75°C	11.4	A
	I _D @T _C =100°C	9.5	A
Pulsed Drain Current ^①	I _{DM}	45	A
Total Power Dissipation	P _D @T _C =25°C	17	W
Total Power Dissipation	P _D @T _A =25°C	0.9	W
Operating Junction Temperature	T _J	-55 to 150	°C
Storage Temperature	T _{STG}	-55 to 150	°C
Single Pulse Avalanche Energy@L=0.1mH	E _{AS}	32	mJ

•Thermal resistance(Q2)

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case ^②	R _{thJC}	-	-	7.1	° C/W
Thermal resistance, junction - ambient	R _{thJA}	-	-	140	° C/W
Soldering temperature, wavesoldering for 10s	T _{sold}	-	-	265	° C

•Electronic Characteristics(Q2)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	30			V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =250uA	1.2		2.5	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V			1.0	uA
Gate- Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V			±100	nA
Static Drain-source On Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =15A		8.0	10.5	mΩ
		V _{GS} =4.5V, I _D =10A		11	14.3	mΩ
Forward Transconductance	g _{FS}	V _{DS} =25V, I _D =10A		10		s
Source-drain voltage	V _{SD}	I _s =15A			1.28	V

•Electronic Characteristics(Q2)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	$V_{DS}=25V$ $f = 1MHz$	-	1150	-	pF
Output capacitance	C_{oss}		-	235	-	
Reverse transfer capacitance	C_{rss}		-	120	-	

•Gate Charge characteristics($T_a = 25^{\circ}C$)(Q2)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	$V_{DD} = 15V$	-	12	-	nC
Gate - Source charge	Q_{gs}	$I_D = 15A$	-	4	-	
Gate - Drain charge	Q_{gd}	$V_{GS} = 10V$	-	6	-	

Note: ① Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;

•characteristics curve(Q1)

Fig.1 Power Dissipation Derating Curve

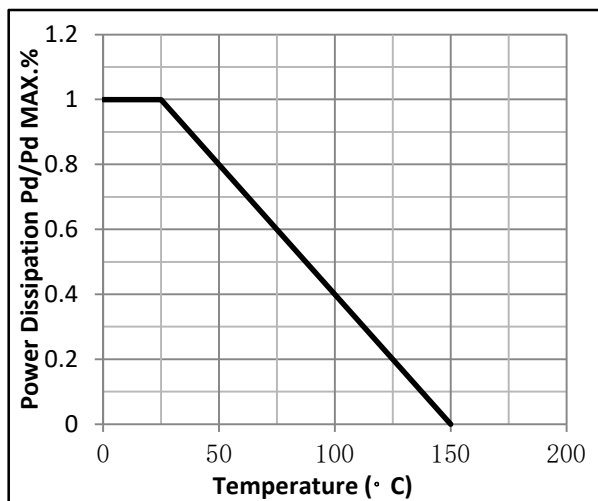


Fig.2 Typical output Characteristics

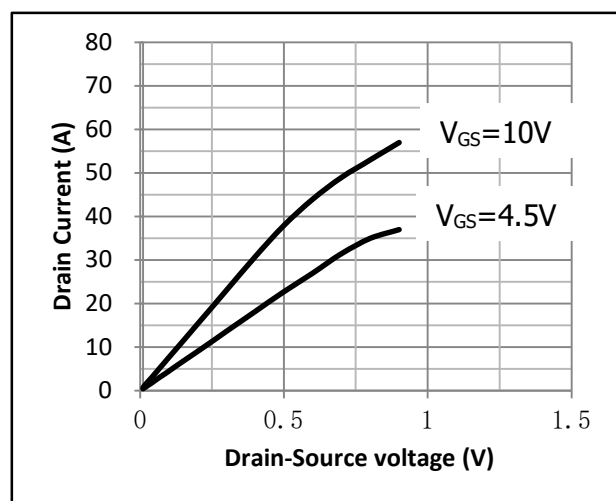


Fig.3 Threshold Voltage V.S Junction Temperature

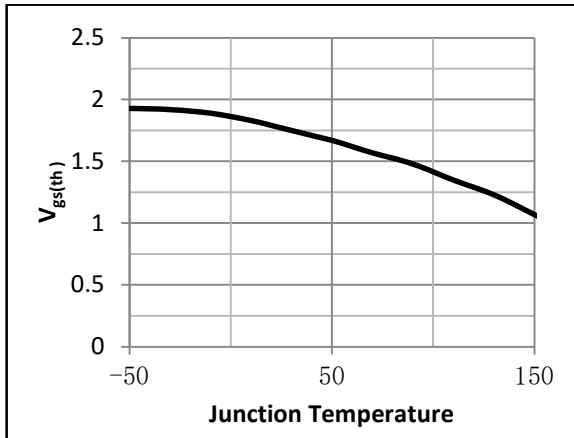


Fig.4 Resistance V.S Drain Current

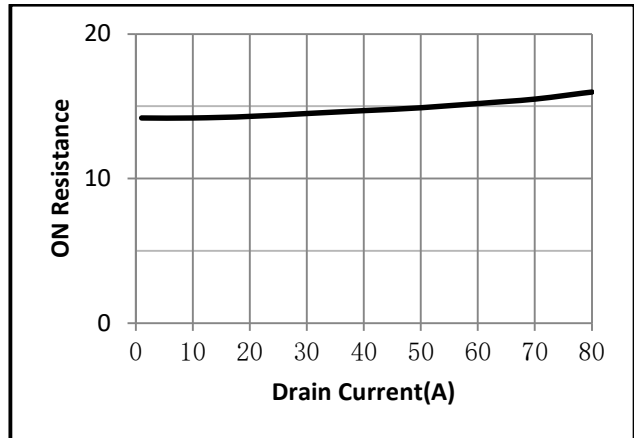


Fig.5 On-Resistance VS Gate Source Voltage

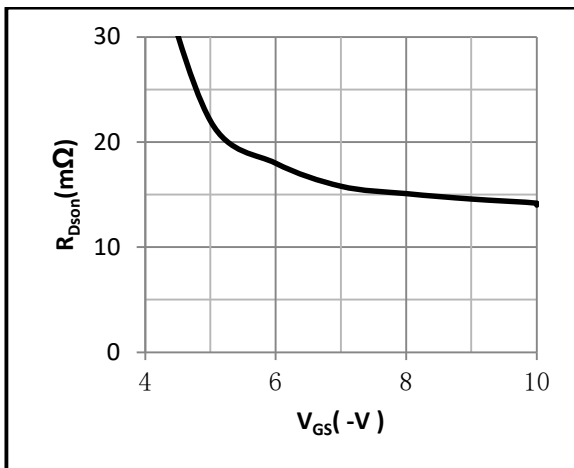
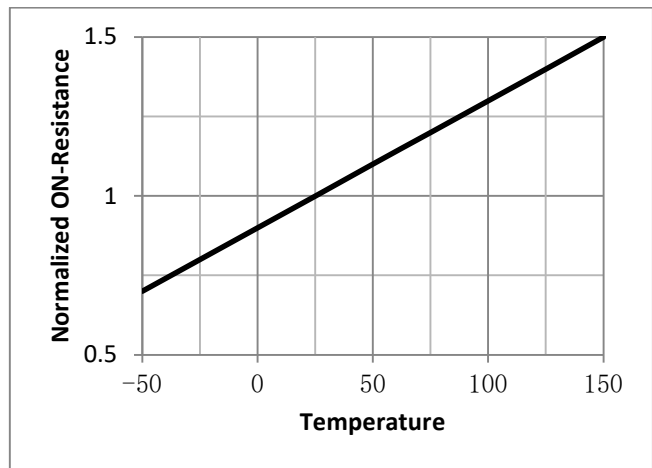


Fig.6 On-Resistance V.S Junction Temperature



•characteristics curve(Q2)

Fig.1 Power Dissipation

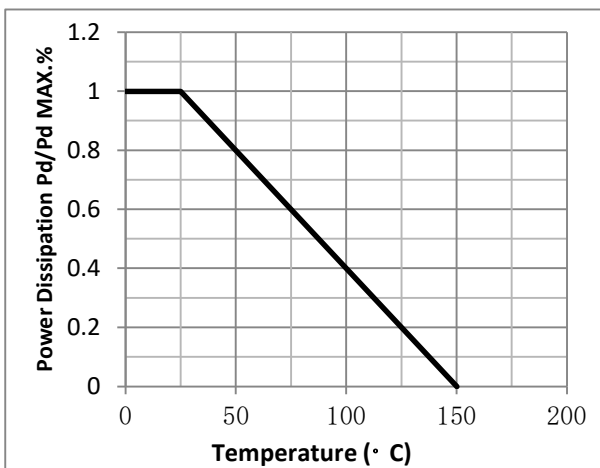


Fig.2 Typical output Characteristics

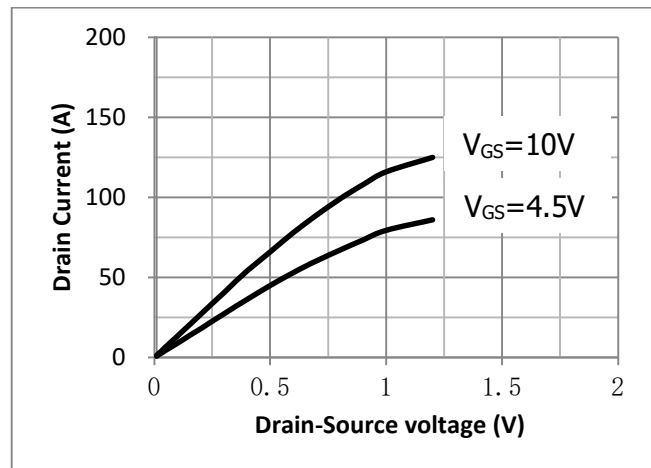


Fig.3 Threshold Voltage V.S Junction Temperature

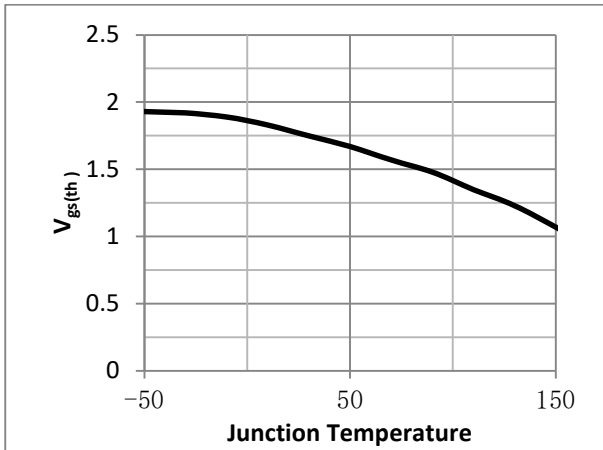


Fig.4 Resistance V.S Drain Current

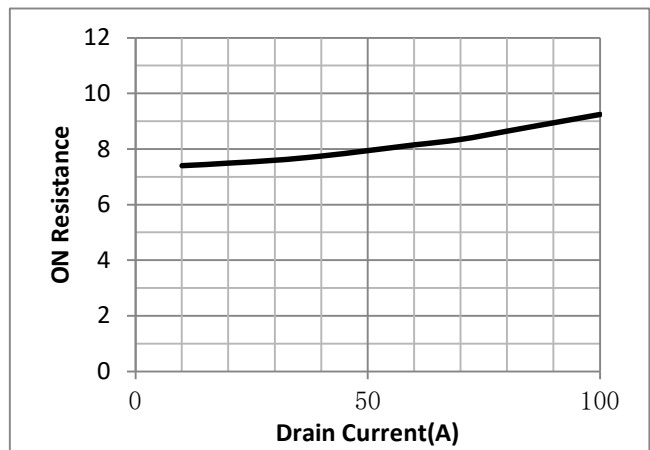


Fig.5 On-Resistance VS Gate Source Voltage

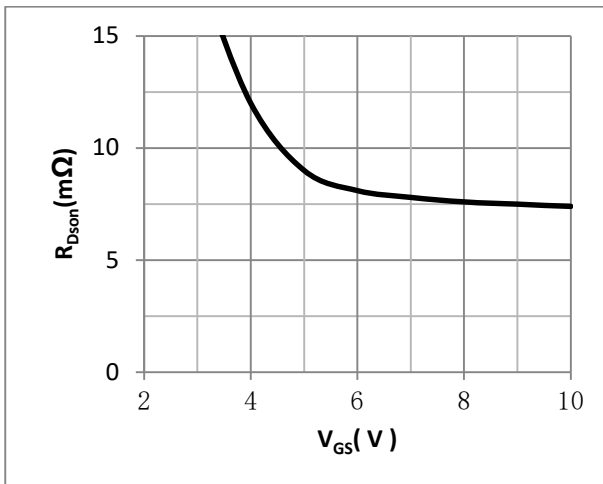
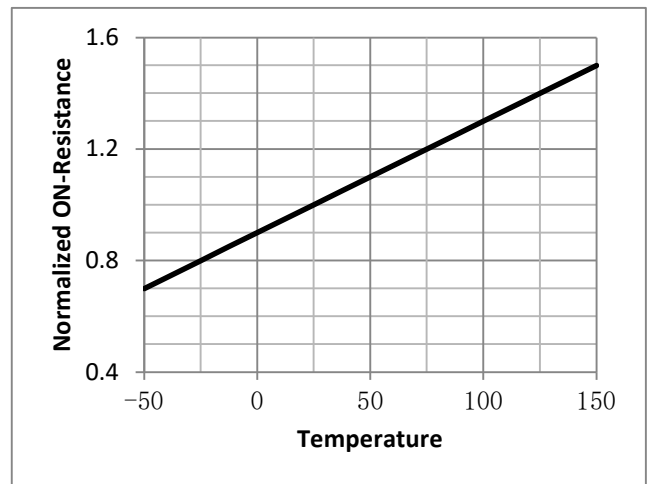


Fig.6 On-Resistance V.S Junction Temperature



•Test Circuit

Fig.1 Gate Charge Measurement Circuit

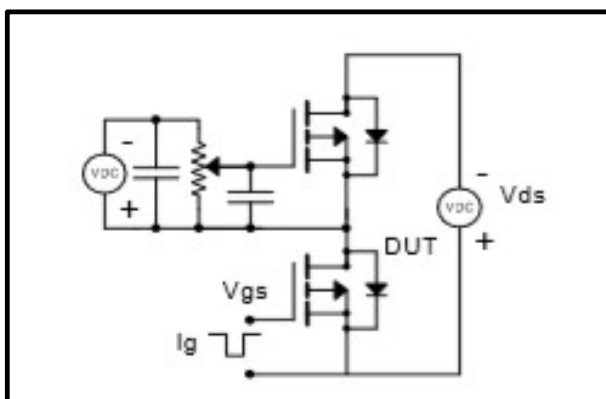


Fig.2 Gate Charge Waveform

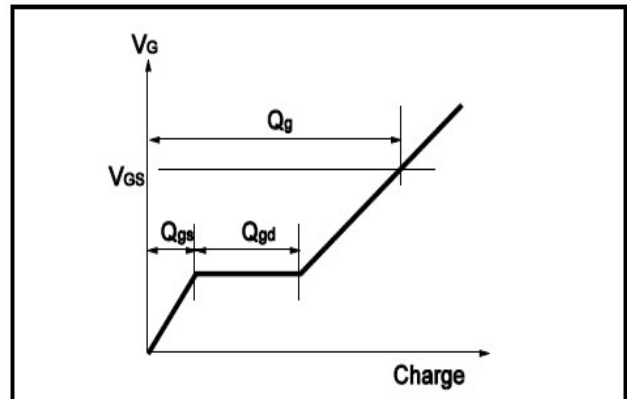


Fig.3 Switching Time Measurement Circuit

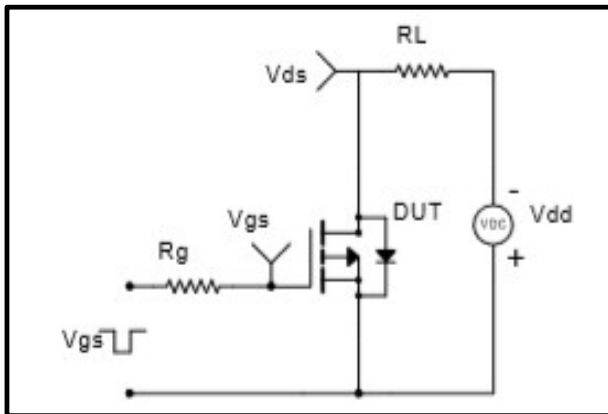


Fig.4 Switching Time Waveform

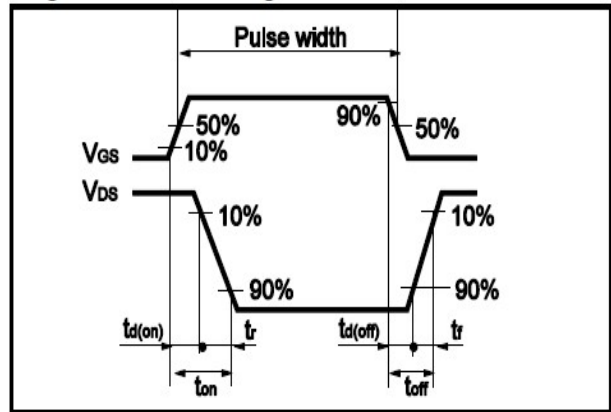


Fig.5 Avalanche Measurement Circuit

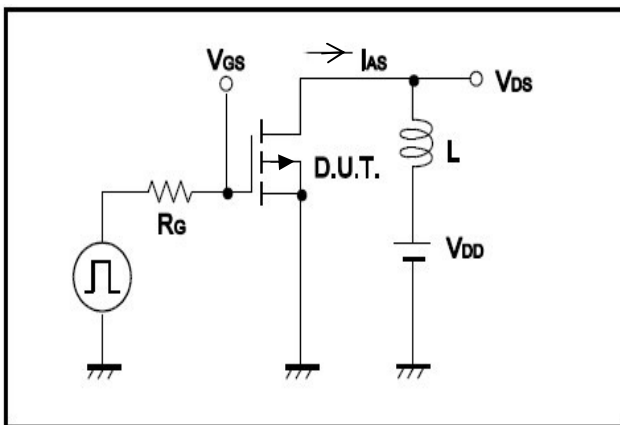
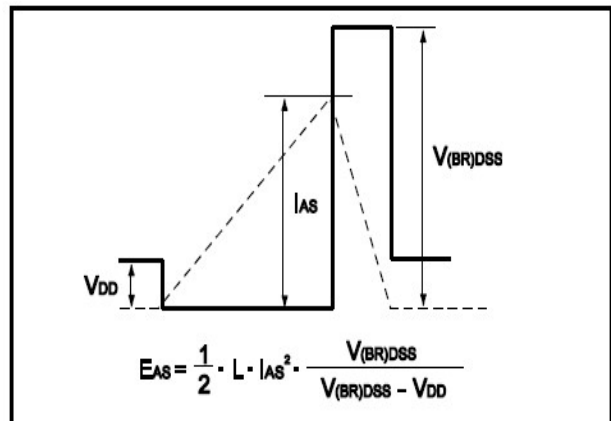
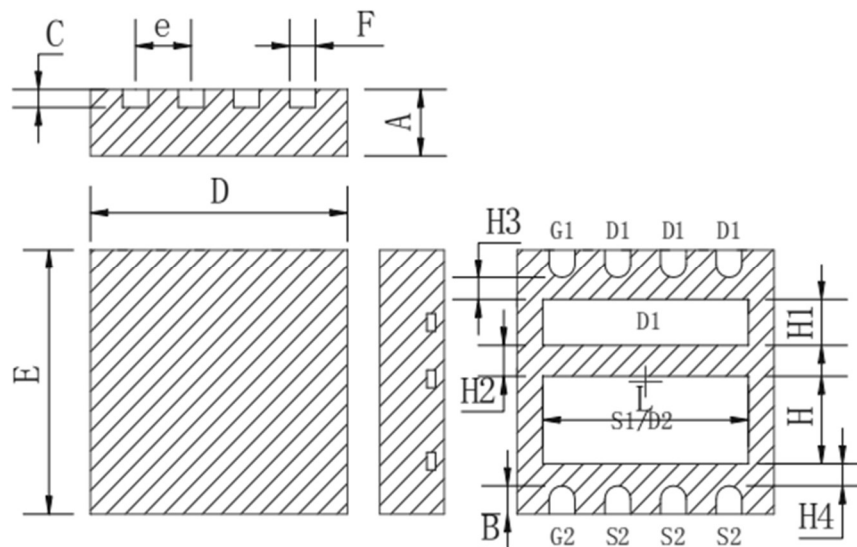


Fig.6 Avalanche Waveform



•Dimensions (DFN3×3)

Unit: mm



Symbol	Min	Typ	Max
A	0.70	0.75	0.80
B	0.27	0.32	0.37
C	0.153	0.203	0.253
D	2.90	3.00	3.10
E	2.90	3.00	3.10
e	0.60	0.65	0.70
F	0.25	0.30	0.35
H	0.89	0.99	1.09
H1	0.42	0.52	0.62
H2	0.25	0.35	0.45
H3	0.15	0.25	0.35
H4	0.15	0.25	0.35
L	2.30	2.40	2.50